

〈Transistor〉

2SC5395

For Low Frequency Amplify Application
Silicon NPN Epitaxial Type Micro(Frame type)

DESCRIPTION

2SC5395 is a silicon NPN epitaxial type transistor. It is designed for low frequency voltage amplify application.

FEATURE

- Small collector to emitter saturation voltage.
 $V_{CE(sat)}=0.3V$ max (@ $I_C=100mA, I_B=10mA$)
- Excellent linearity of DC forward current gain
- Small package for easy mounting

APPLICATION

For small machine low frequency voltage amplify application.

MAXIMUM RATINGS ($T_a=25^{\circ}C$)

SYMBOL	PARAMETER	RATINGS	UNIT
V_{CBO}	Collector to Base voltage	50	V
V_{EBO}	Emitter to Base voltage	6	V
V_{CEO}	Collector to Emitter voltage	50	V
I_C	Collector current	200	mA
P_C	Collector dissipation ($T_a=25^{\circ}C$)	450	mW
T_J	Junction temperature	+125	$^{\circ}C$
T_{stg}	Storage temperature	-55to+125	$^{\circ}C$

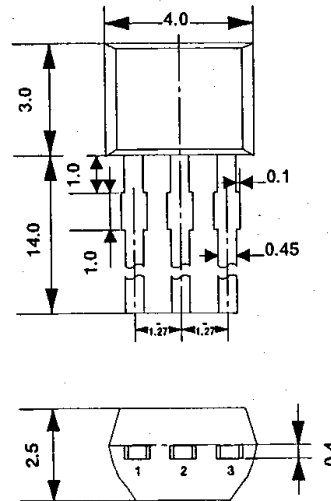
ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}C$)

SYMBOL	PARAMETER	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
$V_{(BR)CEO}$	C to E break down voltage	$I_C=100\mu A, R_{BE}=\infty$	50			V
I_{CBO}	Collector cut off current	$V_{CB}=50V, I_E=0$			0.1	μA
I_{EBO}	Emitter cut off current	$V_{EB}=6V, I_C=0$			0.1	μA
$h_{FE} *$	DC forward current gain	$V_{CE}=6V, I_C=1mA$	150		800	—
h_{FE}	DC forward current gain	$V_{CE}=6V, I_C=0.1mA$	50			—
$V_{CE(sat)}$	C to E saturation voltage	$I_C=100mA, I_B=10mA$			0.3	V
f_T	Gain band width product	$V_{CE}=6V, I_E=-10mA$		200		MHz
C_{ob}	Collector output capacitance	$V_{CB}=6V, I_E=0, f=1MHz$		2.5		pF
NF	Noise figure	$V_{CE}=6V, I_E=-0.1mA, f=1kHz, R_g=2k\Omega$			15	dB

ITEM	E	F	G
h_{FE}	150~300	250~500	400~800

OUTLINE DRAWING

UNIT:mm



TERMINAL CONNECTOR

① : EMITTER
② : COLLECTOR
③ : BASE
EIAJ : —
JEDEC : —

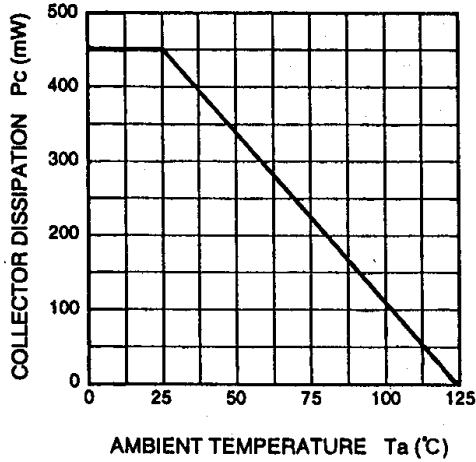
(Transistor)

2SC5395

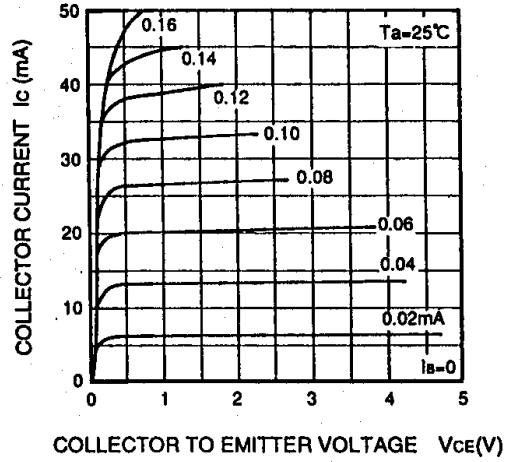
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TYPICAL CHARACTERISTICS

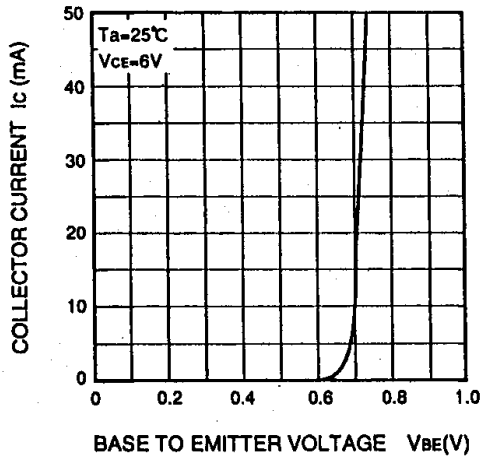
COLLECTOR DISSIPATION
VS. AMBIENT TEMPERATURE



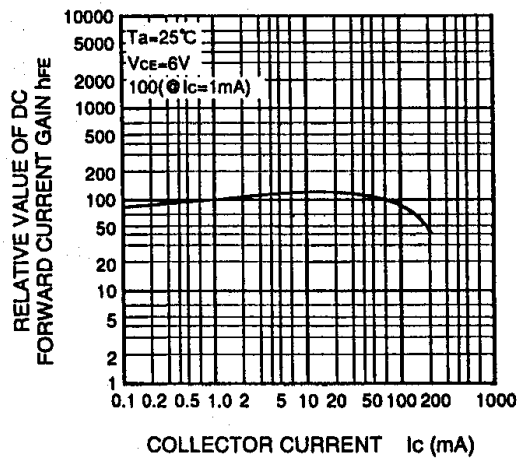
COMMON EMITTER OUTPUT



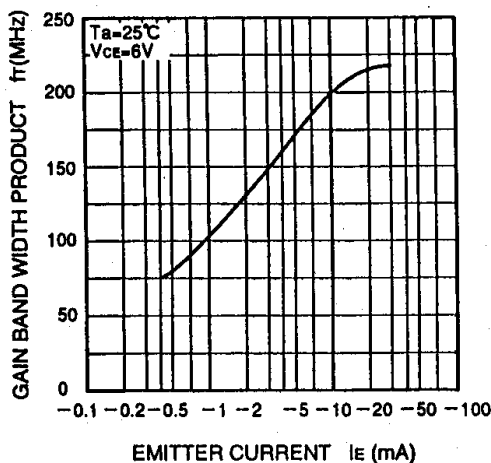
COMMON EMITTER TRANSFER



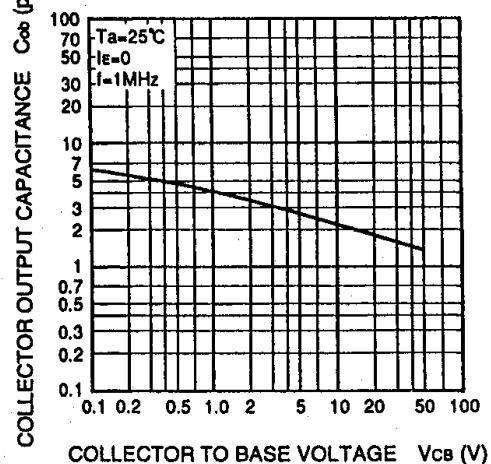
DC FORWARD CURRENT GAIN
VS. COLLECTOR CURRENT



GAIN BAND WIDTH PRODUCT
VS. EMITTER CURRENT



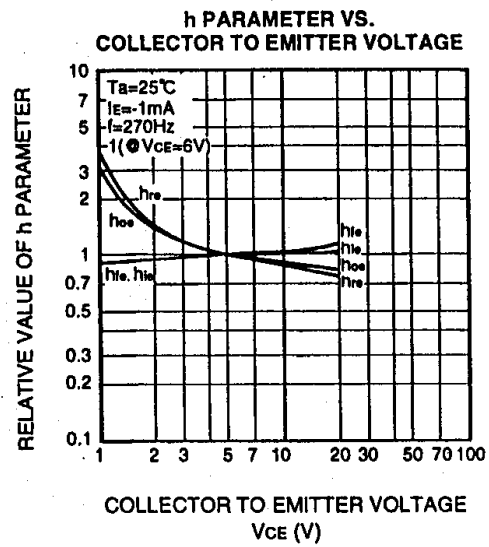
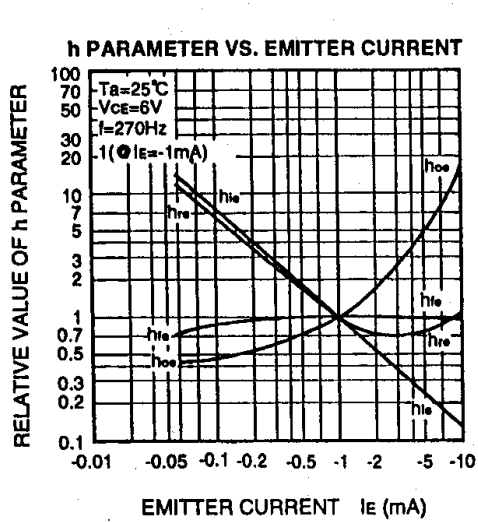
COLLECTOR OUTPUT CAPACITANCE
VS. COLLECTOR TO BASE VOLTAGE



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COMMON EMITTER h PARAMETER (TYPICAL VALUE)

Symbol	Parameter	Test conditions	Limits	Unit
h_{ie}	Closed loop small signal input impedance	$T_a=25^\circ\text{C}$ $V_{CE}=6\text{V}$ $I_E=-1\text{mA}$ $f=270\text{Hz}$	8.5	k Ω
h_{re}	Open loop small signal reverse voltage amplification factor		0.1	$\times 10^{-3}$
h_{fe}	Closed loop small signal forward current amplification factor		300	—
h_{oe}	Open loop small signal output admittance		5.5	μS



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